

ABSTRACT

A method of forming a bonding pad of a semiconductor device is disclosed. An example method forms a first insulating layer over a semiconductor substrate, forms a trench by removing some part of the first insulating layer, forms a top metal interconnect in the trench, forms a second insulating layer over the substrate including the top metal interconnect, and forms a contact hole by removing some part of the second insulating layer, the contact hole exposing a portion of the top metal interconnect. In addition, the example method forms a metal layer on the surface of the second insulating layer and the sidewalls and bottom of the contact hole, forms a metal pad by removing some parts of the metal layer, forms a third insulating layer over the second insulating layer and the metal pad, and exposes the metal pad on the second insulating layer by removing some part of the third insulating layer.